

electrically connected to the leads formed on the wiring board,
the resin sealing step uses a compression-molding process.

112. The method for fabricating the semiconductor device as claimed in claim 111,
wherein a frame having a cavity portion in which the semiconductor element is accommodated is
provided when the wiring board is formed.

113. The method for fabricating the semiconductor device as claimed in claim 111,
C1 cont'd
wherein a film having a detachability with respect to the sealing resin is provided in a position of the
mold facing the wiring board, so that the mold contacts the sealing resin through the film.

114. The method for fabricating the semiconductor device as claimed in claim 111,
wherein a plate member having a detachability with respect to the sealing resin is provided in a
position of the mold facing the wiring board, so that the mold contacts the sealing resin through the
plate member.

115. The method for fabricating the semiconductor device as claimed in claim 114,
wherein the plate member is formed of a substance having a heat radiating performance.

116. The method for fabricating the semiconductor device as claimed in claim 111,
wherein there is provided an excess resin removing mechanism is provided in the mold used in the
resin sealing step,

wherein the excess resin removing mechanism removes excess resin and controls a pressure applied to the sealing resin in the mold.

117. The method for fabricating the semiconductor device as claimed in claim 111, wherein:

extending portions are formed to the wiring board so that the extending portions laterally extend from a position in which the semiconductor element is placed; and

a bending step of bending the extending portions is executed after the resin sealing step is completed and before the protruding electrode forming step is executed.

118. The method for fabricating the semiconductor device as claimed in claim 111, wherein:

extending portions are formed to the wiring board so that the extending portions laterally extend from a position in which the semiconductor element is placed;

a bending step of bending the extending portions is carried out before the resin sealing step is executed; and

the resin sealing step and the protruding electrode forming step are carried out after the bending step is executed.

119. The method for fabricating the semiconductor device as claimed in claim 117, wherein:
connection electrodes to be connected to the semiconductor element are formed to ends
of the extending portions; and

an element connecting step of connecting the semiconductor element and the
connection electrodes is executed after the bending step is carried out.

120. The method for fabricating the semiconductor device as claimed in claim 118,
wherein the connection electrodes are arranged in an interdigital formation, and have curved corners.
